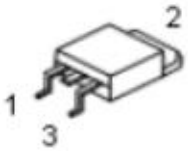
1. Description

The KIA730H N-Channel enhancement mode silicon gate power MOSFET is designed for high voltage,high speed power switching applications such as switching regulators,switching converters,solenoid,motor drivers,relay drivers.

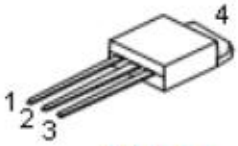
2. Features

- $R_{DS(on)}$=0.83Ω （Typ）@V_{GS}= 10 V
- Low gate charge(typical 20nC)
- Avalanche energy specified
- Fast switching capability
- Improved dv/dt capability

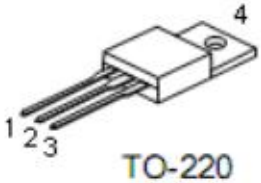
3. Pin configuration



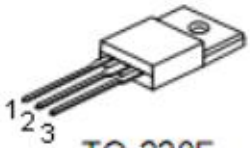
TO-252



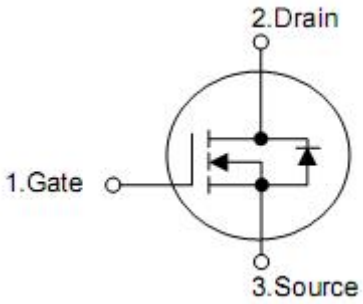
TO-251



TO-220



TO-220F



Pin	Function
1	Gate
2	Drain
3	Source
4	Drain

4. Absolute maximum ratings

(T_C=25 ºC , unless otherwise specified)

Parameter		Symbol	Ratings			Units
			T0251	T0220	T0220F	
Drain-source voltage		V_{DSS}	400			V
Gate-source voltage		V_{GSS}	±30			V
Drain current continuous	T_c=25°C	I_D	6.0*	6.0	6.0*	A
	T_c=100°C		3.6*	3.6	3.6*	A
Drain current pulsed（note1）		I_{DP}	24*	24	24*	A
Avalanche energy	Repetitive (note1)	E_{AR}	7.3			mJ
	Single pulse (note2)	E_{AS}	270			mJ
Peak diode recovery dv/dt (note 3)		dv/dt	4.5			V/ns
Total power dissipation	T_c=25°C	P_D	42	73	38	W
	Derate above 25°C		0.35	0.58	0.30	W/°C
Junction temperature		T_J	+150			°C
Storage temperature		T_{STG}	-55~+150			°C

*Drain current limited by maximum junction temperature

5. Thermal characteristics

Parameter	Symbol	Rating			Unit
		TO251	TO220	TO220F	
Thermal resistance,Junction-to-case	R_{thJC}	2.11	1.71	3.31	ºC/W
Thermal resistance,Junction-to-ambient	R_{thJA}	62.5	62.5	62.5	ºC/W
Thermal resistance, Case-to-sink typ.	R_{thCS}	0.5	0.5	--	ºC/W

6. Electrical characteristics

(T_J=25°C,unless otherwise notes)

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Off Characteristics							
Drain-source breakdown voltage		BV_{DSS}	V_{GS}=0V,I_D=250μA	400	-	-	V
Zero gate voltage drain current		I_{DSS}	V_{DS}=400V ,V_{GS}=0V	-	-	1	μA
			V_{DS}=320V ,T_C=125 ºC	-	-	10	μA
Gate-body leakage current	Forward	I_{GSS}	V_{GS}=30V,V_{DS}=0V	-	-	100	nA
	Reverse		V_{GS}=-30V,V_{DS}=0V	-	-	-100	nA
Breakdown voltage temperature		$\Delta BV_{DSS}/\Delta T_J$	I_D=250μA,	-	0.54	-	V/ºC
On characteristics							
Gate threshold voltage		$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2.0	-	4.0	V
Static drain-source on-resistance		$R_{DS(on)}$	V_{GS}=10V,I_D=3.0A	-	0.83	1.0	Ω
Dynamic characteristics							
Input capacitance		C_{iss}	V_{DS}=25V,V_{GS}=0V, f=1MHz	-	520	-	pF
Output capacitance		C_{oss}		-	80	-	pF
Reverse transfer capacitance		C_{rss}		-	15	-	pF
Switching characteristics							
Turn-on delay time		$t_{d(on)}$	V_{DD}=200V,I_D=6.0A, R_G=25Ω (note4,5)	-	10	-	ns
Rise time		t_r		-	60	-	ns
Turn-off delay time		$t_{d(off)}$		-	20	-	ns
Fall time		t_f		-	40	-	ns
Total gate charge		Q_g	V_{DS}=320V,I_D=6.0A, V_{GS}=10V (note4,5)	-	18	-	nC
Gate-source charge		Q_{gs}		-	2.5	-	nC
Gate-drain charge		Q_{gd}		-	8.5	-	nC
Drain-source diode characteristics							
Drain-source diode forward voltage		V_{SD}	V_{GS}=0V,I_{SD}=6.0A	-	-	1.4	V
Continuous Drain-source current		I_{SD}		-	-	6.0	A
Pulsed Drain-source current		I_{SM}		-	-	24.0	A
Reverse recovery time		t_{rr}	I_{SD}=6.0A, dI_{SD}/dt=100A/μs (note 4)	-	250	-	ns
Reverse recovery charge		Q_{rr}		-	2.0	-	μC

Note: 1.Repetitive Rating:Pulse width limited by maximum junction temperature
2.L=14mH,I_{AS}=6.0A,V_{DD}=50V,R_G=25Ω,Starting TJ=25 ºC
3.I_{SD}≤6.0A,di/dt≤200A/μs, V_{DD}≤ BV_{DSS},Starting TJ=25 ºC
4.Pulse test:pulse width≤300μs,duty cycle≤2%
5.Essentially independent of operating temperature

7. Test circuits and waveforms

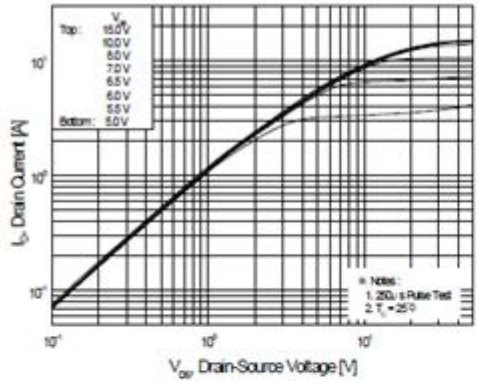


Figure 1. On-Region Characteristics

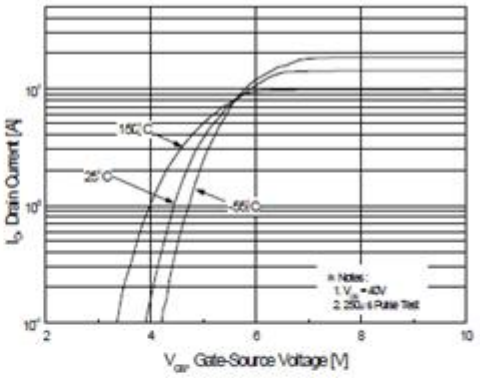


Figure 2. Transfer Characteristics

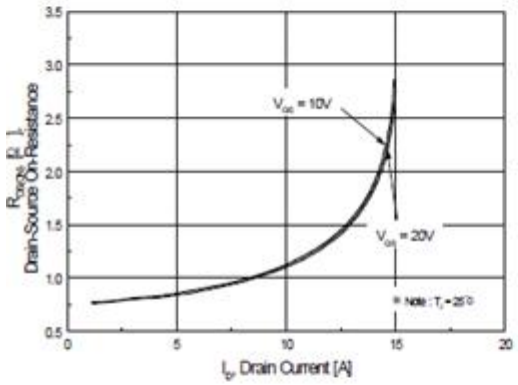


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

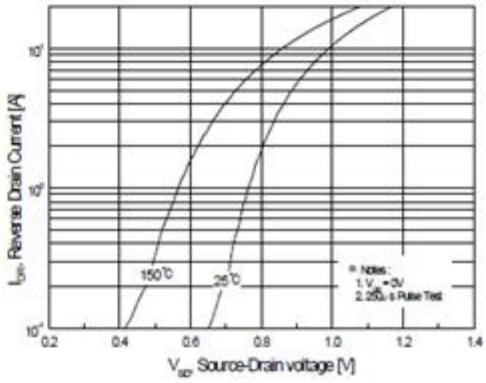


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

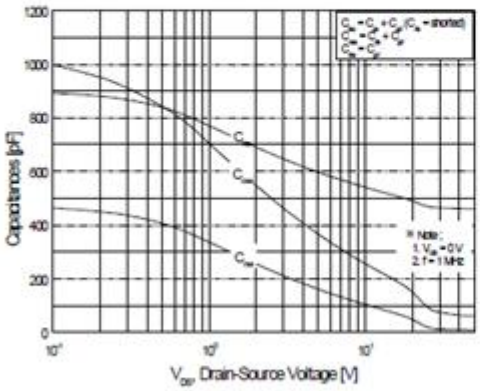


Figure 5. Capacitance Characteristics

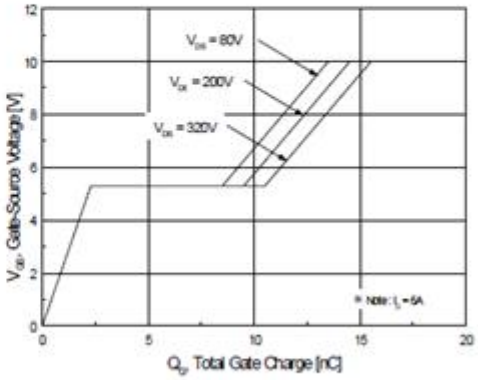


Figure 6. Gate Charge Characteristics

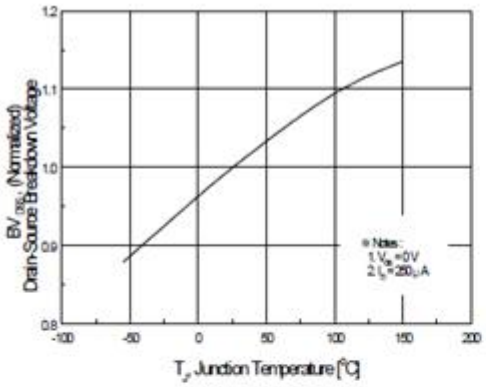


Figure 7. Breakdown Voltage Variation vs Temperature

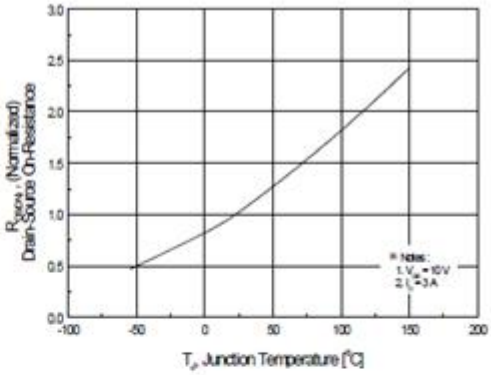


Figure 8. On-Resistance Variation vs Temperature

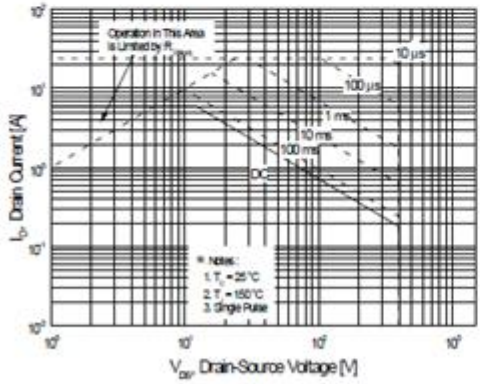


Figure 9-1. Maximum Safe Operating Area for TO220

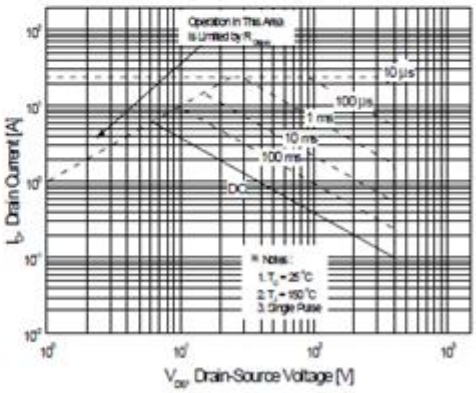


Figure 9-2. Maximum Safe Operating Area for TO220F or TO-251

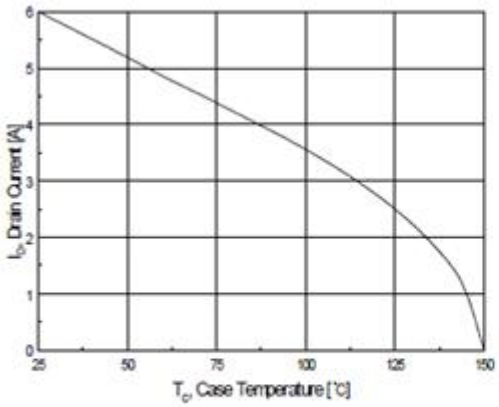


Figure 10. Maximum Drain Current vs Case Temperature

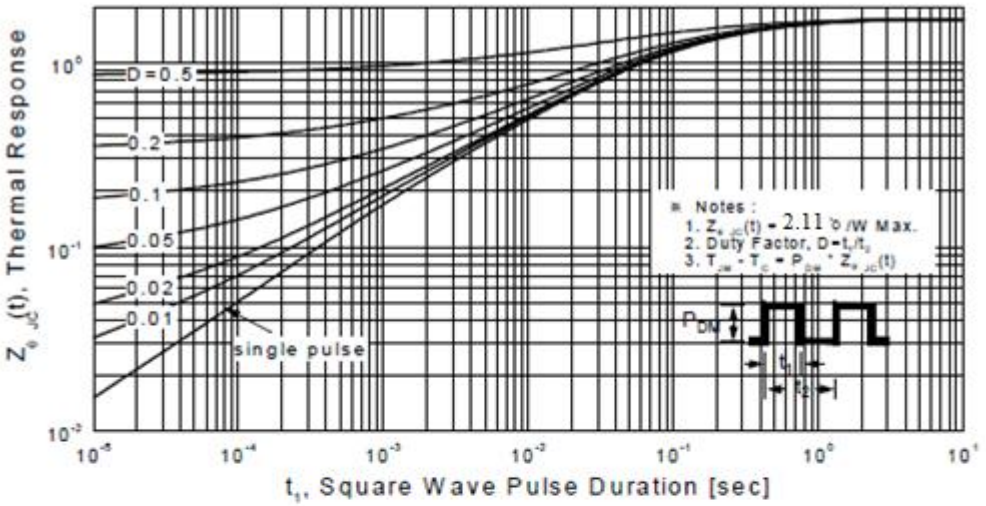


Figure 11-1. Transient Thermal Response Curve for or TO-251

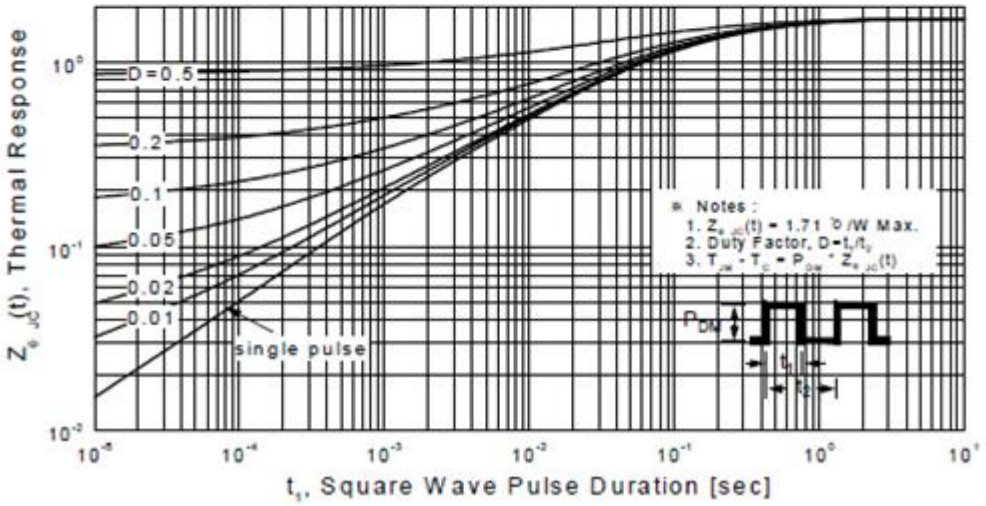


Figure 11-2. Transient Thermal Response Curve for TO220

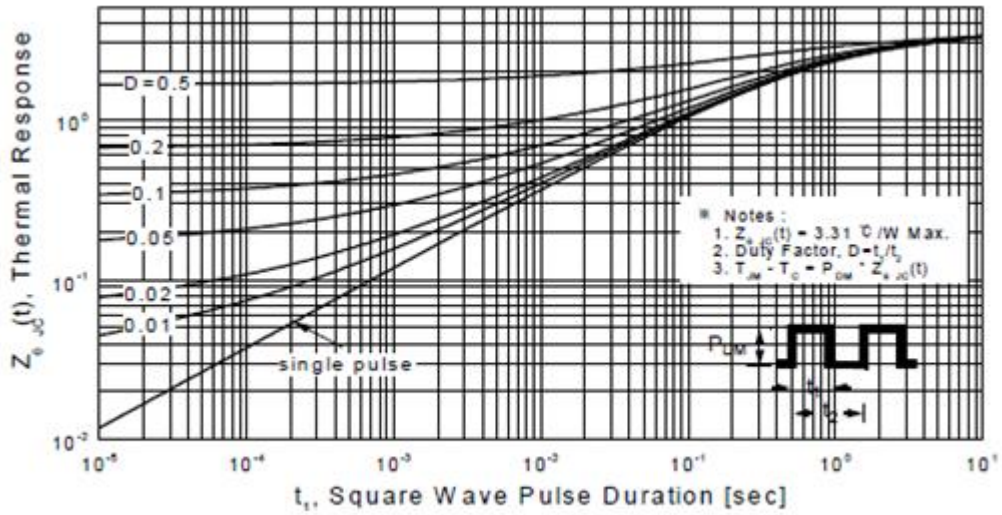


Figure 11-3 Transient Thermal Response Curve for TO220F